### **Vishay Semiconductors**

Hyperfast Rectifier, 3 A FRED Pt®



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DESIGN SUPPORT TOOLS



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	3 A			
V <sub>R</sub>	200 V			
V <sub>F</sub> at I <sub>F</sub>	0.74 V			
t <sub>rr</sub>	30 ns			
T <sub>J</sub> max.	175 °C			
Package	SlimSMA (DO-221AC)			
Circuit configuration	Single			

#### **FEATURES**

• Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



COMPLIANT HALOGEN

FREE

- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- · Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V		
Average rectified forward current	I <sub>F(AV)</sub>	$T_{\rm C} = 145 \ ^{\circ}{\rm C}^{(1)}$	3	٨		
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	85	A		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

#### Note

<sup>(1)</sup> Device on PCB with 8 mm x 16 mm soldering lands

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 $^{\circ}$ C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-	
Forward voltage	VF	I <sub>F</sub> = 3 A	-	0.86	0.93	V
i orward voltage	VF	I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C	-	0.74	0.78	
Reverse leakage current	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	2	
		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1	8	μA
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	13	-	pF



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, dI_F/dt = 50$	0 Α/μs, V <sub>R</sub> = 30 V	-	26	-		
Reverse recovery time	+	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	30		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	18	-	ns	
		T <sub>J</sub> = 125 °C		-	26	-		
Deals receiver a current		T <sub>J</sub> = 25 °C	$I_F = 3 A$	-	2.5	-	А	
Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 160 V	-	4	-	A		
Reverse recovery charge Q <sub>rr</sub>	0	T <sub>J</sub> = 25 °C		-	23	-	nC	
	Qrr	T <sub>J</sub> = 125 °C		-	50	-	no	

<b>THERMAL - MECHANICAL SPECIFICATIONS</b> ( $T_J$ = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to lead	R <sub>thJL</sub>	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	8	10	°C/W	
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	91	110	C/W	
Approvimate Waight				0.032		g	
Approximate Weight				0.0011		oz.	
Marking device		Case style SlimSMA (DO-221AC)		31	H2		

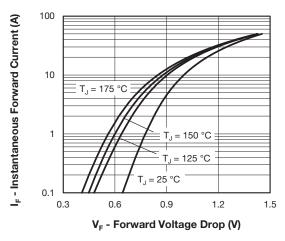


Fig. 1 - Typical Forward Voltage Drop Characteristics

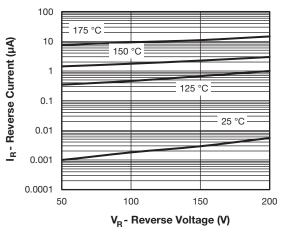


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



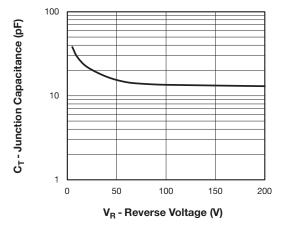


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

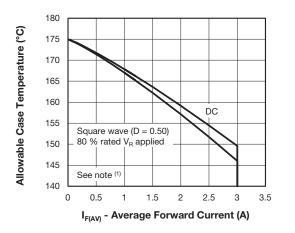


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

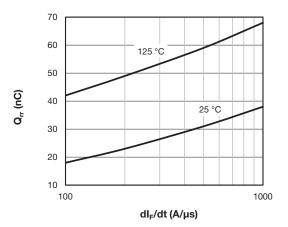


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{Fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

3.5 **RMS** limit 3 Average Power Loss (W) 2.5 2 D = 0.201.5 D = 0.25D = 0.33 1 D = 0.50 D = 0.75 DC 0.5 0 0 0.6 1.2 1.8 2.4 3 3.6 4.2 4.8

Average Forward Current - I<sub>F(AV)</sub> (A)

Fig. 5 - Forward Power Loss Characteristics

VS-3EJH02HM3

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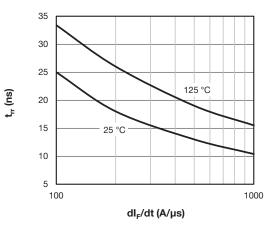
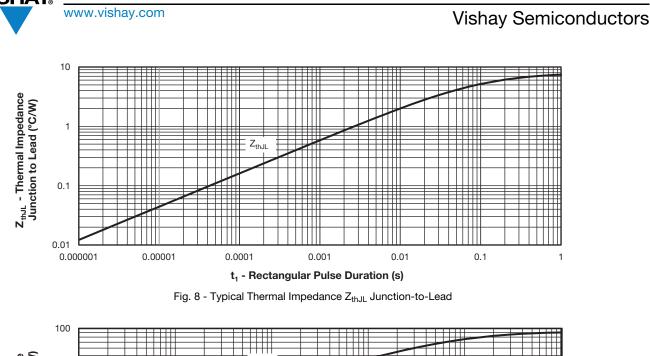


Fig. 6 - Typical Reverse Recovery vs. dl<sub>F</sub>/dt

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VS-3EJH02HM3

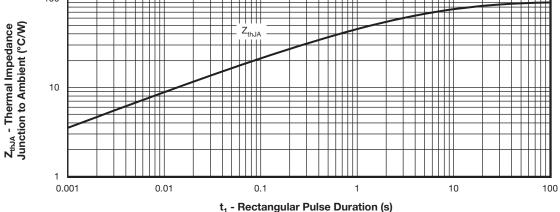
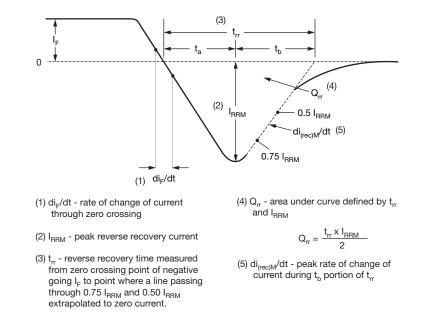
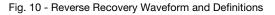


Fig. 9 - Typical Thermal Impedance ZthJA Junction-to-Ambient





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Device code	VS-	3	Е	J	н	02	н	М3
		2	3	4	5	6	7	8
	1 · 2 · 3 ·	Cur	rent rati	niconduo ng (3 = iguration	3 A)	oduct		
	4 - 5 -	E = J =	single c	liode A packa				
	6 - 7 - 8 -	· Volt · H =	age coo AEC-Q	ast recov de (02 = 101 qua en-free,	200 V) alified	complia	nt, and	termina

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-3EJH02HM3/6A	3500	3500	7"diameter plastic tape and reel				
VS-3EJH02HM3/6B	14 000	14 000	13"diameter plastic tape and reel				

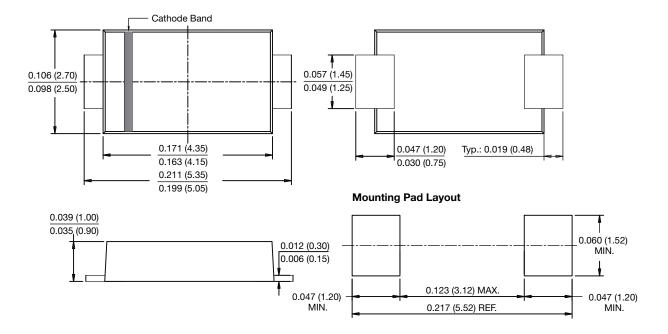
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95571				
Part marking information	www.vishay.com/doc?95562				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96050				



**Vishay Semiconductors** 

# DO-221AC (SlimSMA)

### **DIMENSIONS** in inches (millimeters)





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